P0120007P

250mW GaAs Power FET (Pb-Free Type)

Technical Note

SUMITOMO ELECTRIC

♦Features

· Up to 2.7 GHz frequency band
· Beyond +22 dBm output power
· Up to +41dBm Output IP3
· High Drain Efficiency
· 15dB Gain at 2.1GHz
· SOT-89 SMT Package
· Low Noise Figure

♦Applications

· Wireless communication system
· Cellular, PCS, PHS, W-CDMA, WLAN

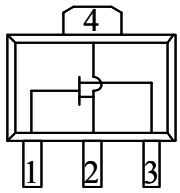
♦Description

P0120007P is a high performance GaAs MESFET housed in a low-cost SOT-89 package. Our originally developed "pulse-doped" channel structure has realized low distortion, which leads to high IP3. The channel structure also achieved an extremely low noise figure. The details about pulse-doped FET channel are described in our products catalog. Utilization of AuSn die attach has realized a low and stable thermal resistance. ***The lead frame is plated with Sn-Bi to make the device Pb-free.***

SEI's long history of manufacturing has cultivated high device reliability. The estimated MTTF of the FET is longer than 15years at Tj of 150°C. You can see the details in ***Reliability and Quality Assurance.***

♦Functional Diagram

Pin No.	Function
1	Input/Gate
2, 4	Ground
3	Output/Drain



♦Ordering Information

Part No	Description	Number of devices	Container
P0120007P	GaAs Power FET	1000	7" Reel
KP027J	2.11-2.17GHz Application Circuit	1	Anti-static Bag

♦Absolute Maximum Ratings (@Tc=25°C)

Parameter	Symbol	Value	Units
Drain-Source Voltage	Vds	10	V
Gate-Source Voltage	Vgs	- 4	V
Drain Current	Ids	Idss	---
RF Input Power (continuous)	Pin	13 (*)	dBm
Power Dissipation	Pt	2.1	W
Junction Temperature	Tj	150 (**)	°C
Storage Temperature	Tstg	- 40 to +150	°C

Tc: Case Temperature. Operating the device beyond any of these values may cause permanent damage.
(*) Measured at 2.1GHz with our test fixture matched to IP3.
(**) Recommended Tj under operation is below 125°C.

♦Electrical Specifications (@Tc=25°C)

Parameter		Symbol	Test Conditions	Values			Units
				Min.	Typ.	Max.	
DC	Saturated Drain Current	Idss	Vds=3V, Vg=0V	---	---	300	mA
	Transconductance	gm	Vds=8V, Ids=100mA	90	---	---	mS
	Pinchoff Voltage	Vp	Vds=8V, Ids=10mA	- 3.0	---	- 1.7	V
	Gate-Source Breakdown Voltage	|Vgs0|	Igso= - 10μA	3.0	---	---	V
	Thermal Resistance	Rth	Channel-Case	---	---	60	°C/W
RF	Frequency	f				2.7	GHz
	Output Power @ 1dB Gain Compression	P1dB	Vds=8V Ids=80mA f=2.1GHz		24	---	dBm
	Small Signal Gain	G			15	---	dB
	Output IP3	IP3		---	41	---	dBm
	Power Added Efficiency	η_{add}		---	38	---	%

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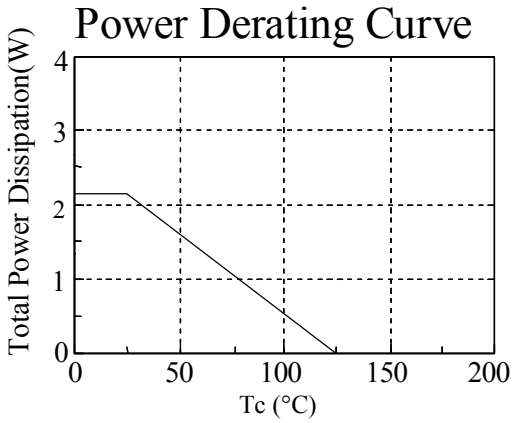
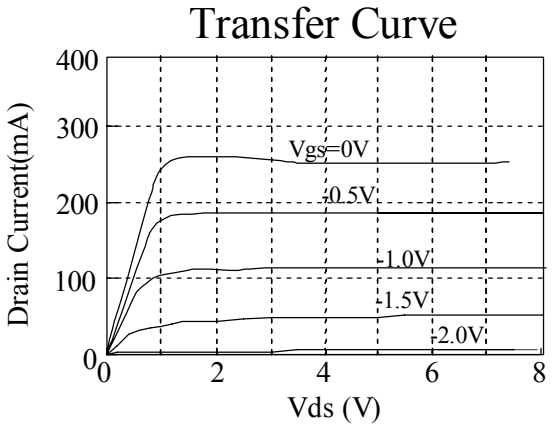
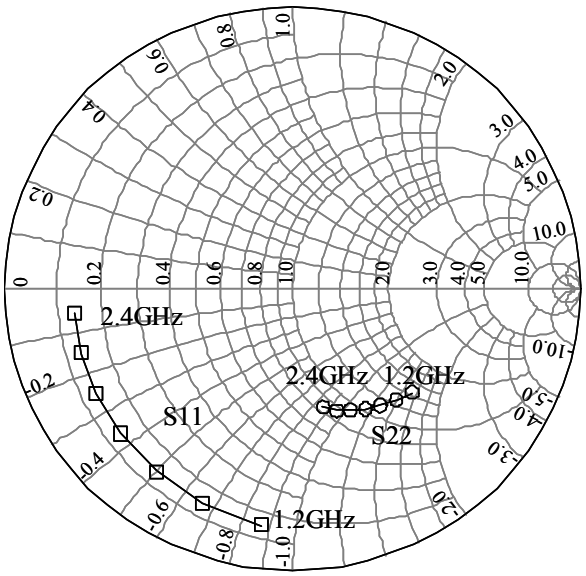
♦Typical Characteristics

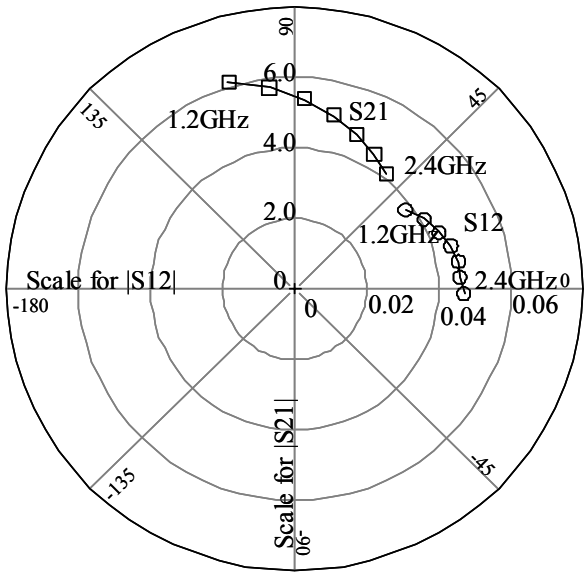




♦Load-pull Characteristics (Typical Data)

Tc=25°C, Vds=8V, **Ids=100mA,** Common Source, Zo=50Ω (Calibrated to device leads)





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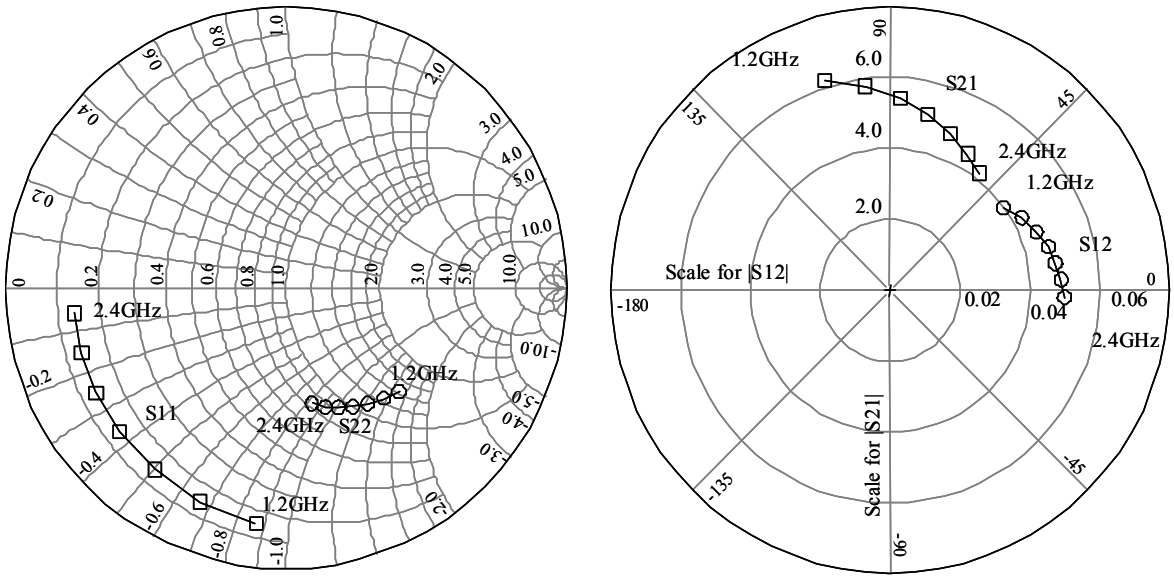
Tc=25°C, Vds=8V, **Ids=80mA,** Common Source, Zo=50Ω (Calibrated to device leads)



=100mA

Freq(GHz)	S11 Mag	S11Ang	S21 Mag	S21 Ang	S12 Mag	S12 Ang	S22 Mag	S22 Ang
1.2	0.847	-97.5	6.148	107.5	0.038	36.0	0.555	-41.6
1.4	0.823	-112.3	5.764	97.0	0.041	28.8	0.534	-47.6
1.6	0.800	-126.2	5.392	87.0	0.043	21.9	0.513	-53.8
1.8	0.787	-139.5	5.038	77.6	0.045	15.6	0.495	-59.4
2.0	0.776	-151.5	4.702	68.6	0.046	9.7	0.474	-65.1
2.2	0.769	-162.7	4.407	60.2	0.046	4.1	0.458	-70.5
2.4	0.761	-173.4	4.133	52.3	0.047	-1.6	0.433	-76.0

=80mA

Freq(GHz)	S11 Mag	S11Ang	S21 Mag	S21 Ang	S12 Mag	S12 Ang	S22 Mag	S22 Ang
1.2	0.846	-97.3	6.188	107.5	0.040	35.7	0.547	-42.5
1.4	0.821	-112.1	5.802	97.0	0.043	28.5	0.525	-48.6
1.6	0.798	-126.1	5.428	87.1	0.045	21.4	0.503	-54.9
1.8	0.785	-139.3	5.071	77.6	0.047	15.1	0.484	-60.6
2.0	0.774	-151.4	4.734	68.7	0.048	9.1	0.463	-66.4
2.2	0.766	-162.5	4.437	60.3	0.049	3.5	0.446	-71.8
2.4	0.759	-173.3	4.159	52.3	0.050	-2.3	0.421	-77.3

[Note] You can download the S-parameter list from our web site: www.sei.co.jp/GaAsIC/

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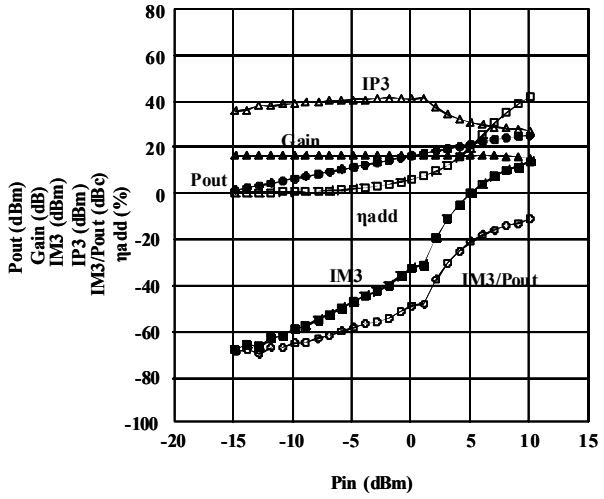
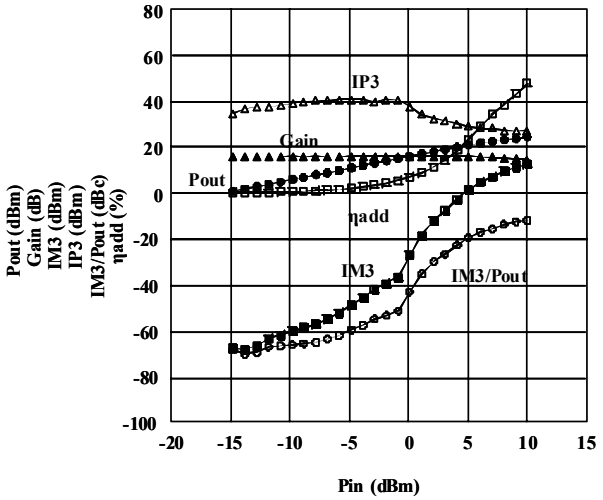
Ids=100mA



Device: P0120007P
Frequency: f1=2.1GHz f2=2.101GHz
Bias: Vds=8V, Ids=100mA
Source Matching: Mag 0.68 Ang 133.9°
Load Matching: Mag 0.37 Ang 91.1°

Ids=80mA



Device: P0120007P
Frequency: f1=2.1GHz f2=2.101GHz
Bias: Vds=8V, Ids=80mA
Source Matching: Mag 0.68 Ang 133.9°
Load Matching: Mag 0.54 Ang 77.8°

[Note] P_{out} and η_{add} are measured by one signal.

The data for the figures above were measured with the load impedance matched to IP3.

Id=100mA

Pin (dBm)	Pout (dBm)	Gain (dB)	IM3 (dBm)	IM3/Pout (dBc)	IP3 (dBm)	Id (mA)	ηadd (%)
-15.0	1.2	16.2	-68.1	-69.3	35.9	97.8	0.2
-10.0	6.3	16.3	-59.2	-65.5	39.0	95.3	0.5
-5.0	11.4	16.4	-47.5	-58.8	40.8	91.7	1.8
0.0	16.4	16.4	-32.8	-49.2	41.0	88.2	6.0
5.0	21.4	16.4	0.1	-21.3	30.7	85.1	19.8
10.0	25.1	15.1	13.8	-11.3	27.1	93.3	41.9

Id=80mA

Pin (dBm)	Pout (dBm)	Gain (dB)	IM3 (dBm)	IM3/Pout (dBc)	IP3 (dBm)	Id (mA)	ηadd (%)
-15.0	0.7	15.7	-67.8	-68.5	34.9	78.9	0.2
-10.0	5.9	15.9	-60.3	-66.2	39.0	76.1	0.6
-5.0	11.0	16.0	-48.9	-59.8	40.9	72.6	2.1
0.0	16.1	16.1	-27.3	-43.3	37.7	69.9	7.0
5.0	21.0	16.0	1.5	-19.5	29.1	65.0	23.6
10.0	24.4	14.4	12.4	-12.0	27.2	69.6	47.8

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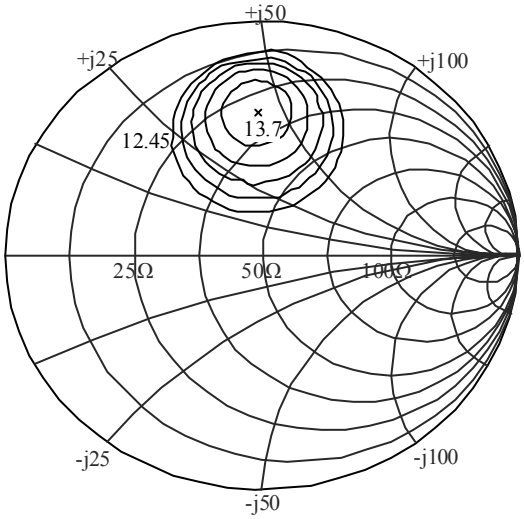
Tc= 25°C, Vds=8V, Ids=100mA, Pin=-5dBm

[Pout-Lstate]

f = 2.1GHz

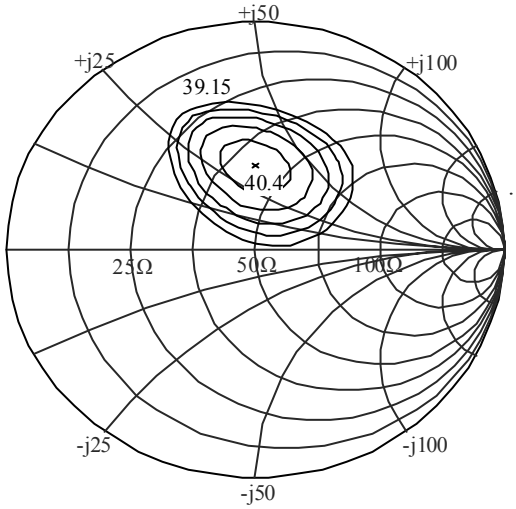
Γ_{pout} : 0.61∠ 92.7
Source : 0.65∠ 154.2
Pout max : 13.7dBm



[IP3-Lstate]

f1 = 2.1GHz
f2 = 2.101GHz

Γ_{IP3} : 0.37∠ 91.1
Source : 0.68∠ 133.9
IP3 max : 40.4dBm

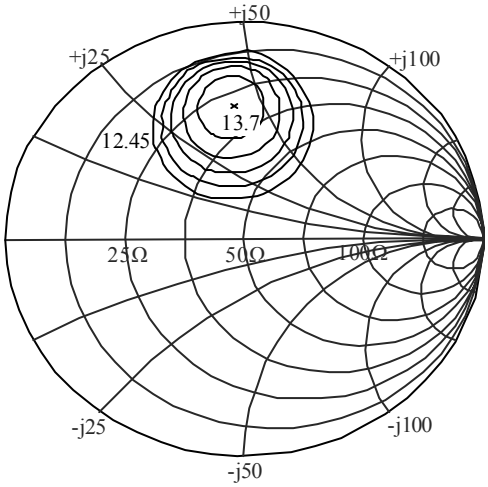


Tc=25°C, Vds=8V, Ids=80mA, Pin=-5dBm

[Pout-Lstate]

f = 2.1GHz

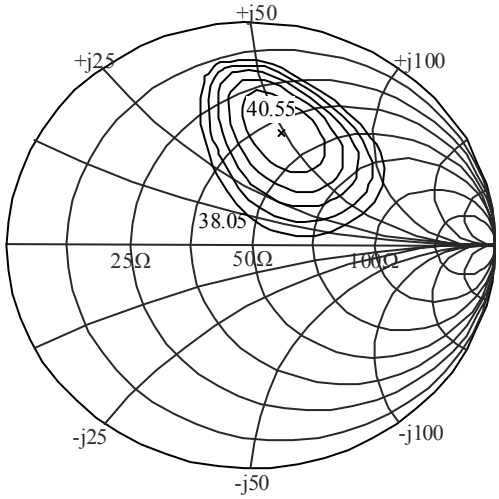
Γ_{pout} : 0.63∠ 94.2
Source : 0.65∠ 154.2
Pout max : 13.7dBm



[IP3-Lstate]

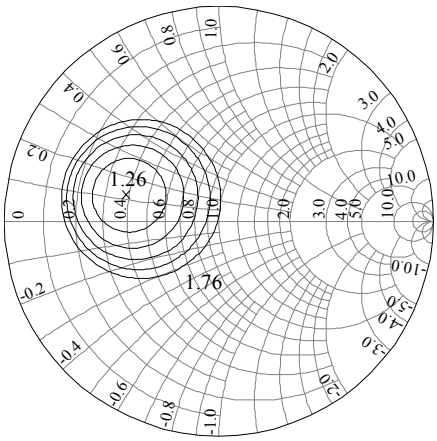
f1 = 2.1GHz
f2 = 2.101GHz

Γ_{IP3} : 0.54∠ 77.8
Source : 0.68∠ 133.9
IP3 max : 40.55dBm

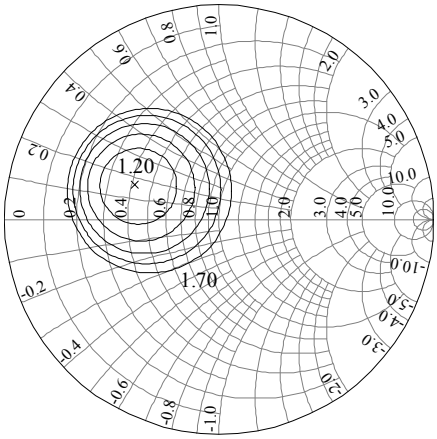


♦NF Characteristics

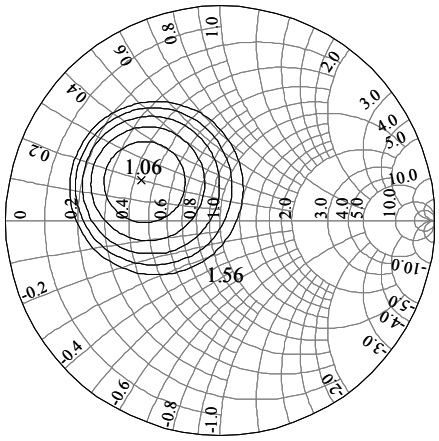
Ids=100mA



Ids=80mA



Ids=60mA



[Note] The data for Smith charts were measured at frequency of 2GHz and Tc of 25°C.

Vds=8V Ids=100mA

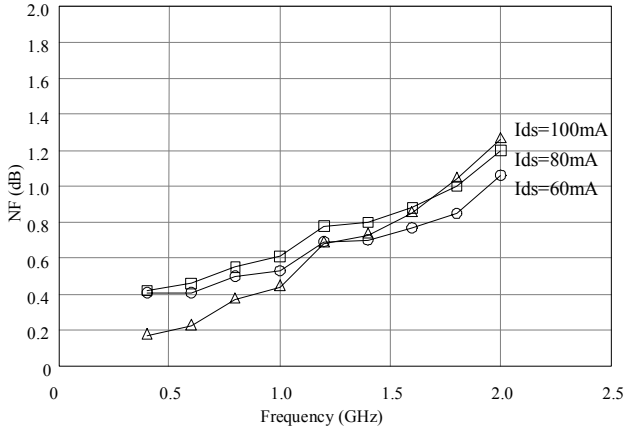
Freq. (GHz)	NFmin (dB)	Γopt Mag	Γopt Ang(deg)	Rn/50	Associated Gain(dB)
0.4	0.17	0.70	-96.6	0.14	23.8
0.6	0.22	0.64	-67.5	0.22	21.7
0.8	0.37	0.58	-35.8	0.27	20.3
1.0	0.44	0.57	-0.6	0.33	19.6
1.2	0.68	0.49	30.4	0.31	18.3
1.4	0.73	0.52	64.9	0.25	17.7
1.6	0.85	0.51	97.5	0.19	17.1
1.8	1.04	0.50	129.5	0.11	16.4
2.0	1.26	0.45	163.8	0.07	15.9

Vds=8V Ids=60mA

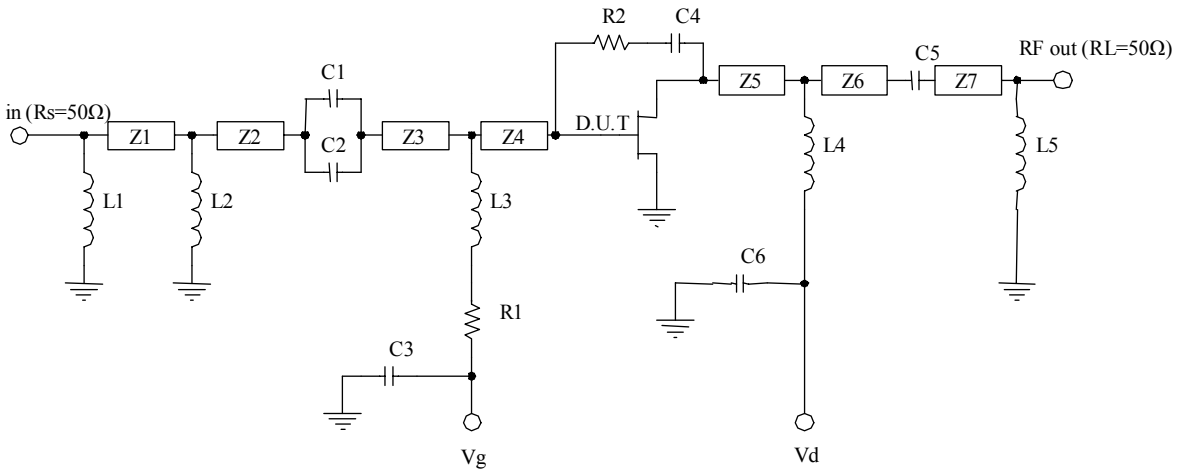
Freq. (GHz)	NFmin (dB)	Γopt Mag	Γopt Ang(deg)	Rn/50	Associated Gain(dB)
0.4	0.41	0.69	-100.2	0.13	23.5
0.6	0.41	0.65	-70.8	0.19	21.5
0.8	0.50	0.58	-42.0	0.25	19.9
1.0	0.53	0.54	-7.8	0.25	19.1
1.2	0.69	0.47	21.1	0.30	18.0
1.4	0.70	0.50	54.7	0.23	17.2
1.6	0.77	0.49	87.0	0.18	16.6
1.8	0.85	0.47	117.6	0.11	15.9
2.0	1.06	0.41	152.9	0.07	15.7

Vds=8V Ids=80mA

Freq. (GHz)	NFmin (dB)	Γopt Mag	Γopt Ang(deg)	Rn/50	Associated Gain(dB)
0.4	0.42	0.70	-98.3	0.14	23.9
0.6	0.46	0.64	-69.0	0.21	21.8
0.8	0.55	0.58	-39.2	0.27	20.3
1.0	0.61	0.54	-4.8	0.27	19.4
1.2	0.78	0.49	25.7	0.32	18.3
1.4	0.80	0.50	59.3	0.25	17.6
1.6	0.88	0.49	91.1	0.19	16.9
1.8	1.00	0.48	123.2	0.12	16.3
2.0	1.20	0.43	157.5	0.08	16.0

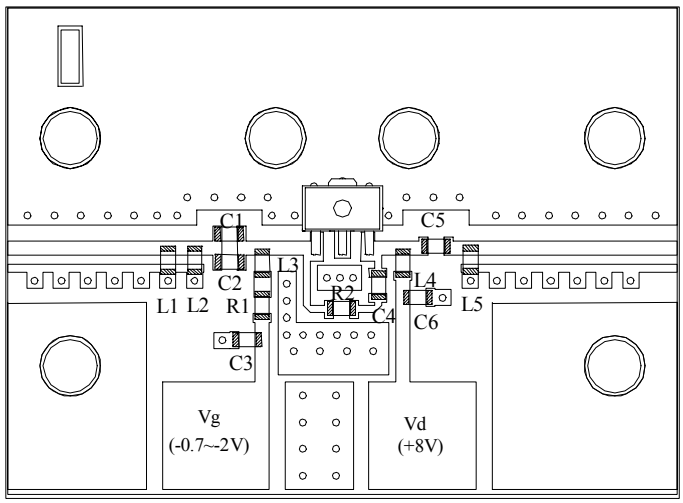


♦Application Circuit : 2110-2170MHz



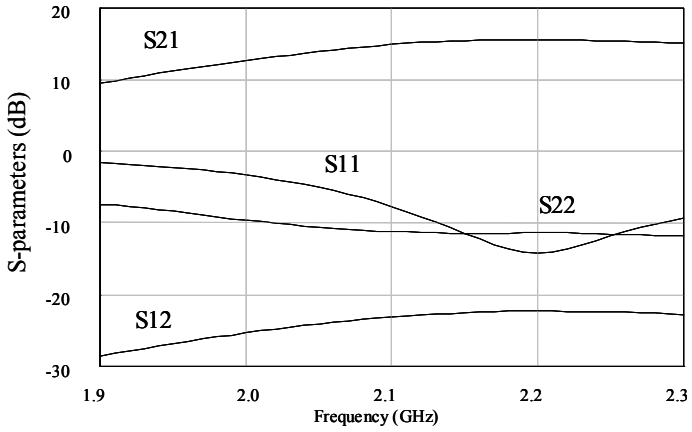
KP027J

RF in



RF out

Ref. Des.	Value	Part Number
R1	82Ω	SUSUMU RR0816 series
R2	470Ω	
C1	0.5pF	MURATA GRM18 series
C2	0.75pF	
C3	0.1μF	
C4	0.5pF	
C5	6pF	
C6	0.1μF	
L1	3.3nH	TOKO LL1608 series
L2	3.3nH	
L3	18nH	
L4	18nH	
L5	2.7nH	

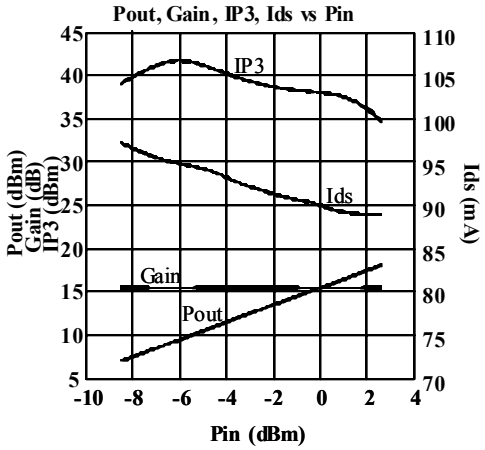


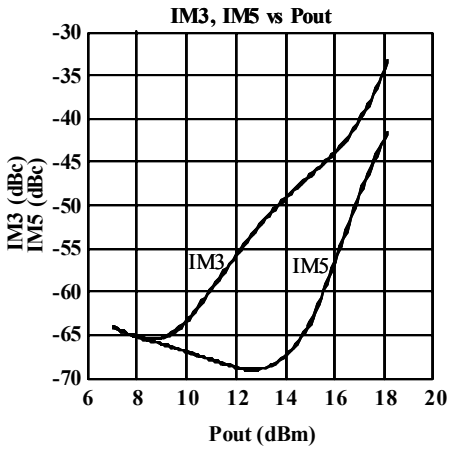
Ref. Designator	Electrical length @ 2.1GHz (deg)
Z1	5.9
Z2	5.44
Z3	4.08
Z4	13.61
Z5	8.62
Z6	6.38
Z7	3.63

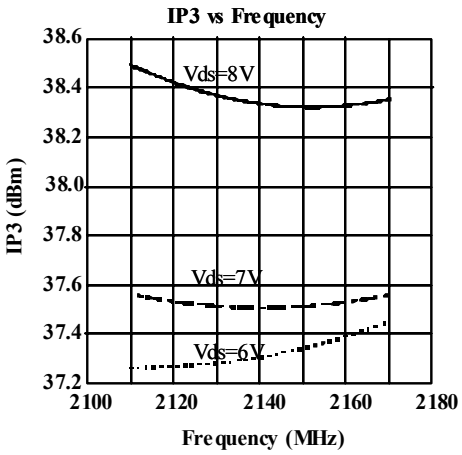
All microstrip lines have a line impedance of 50Ω.

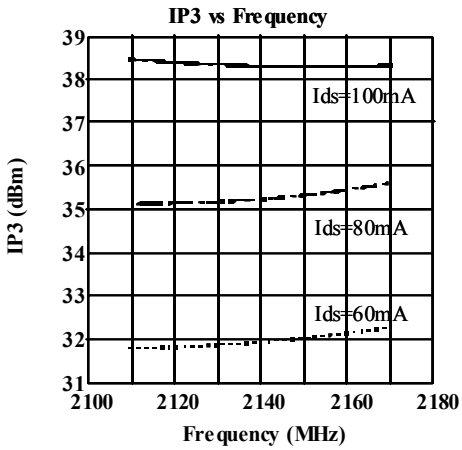
[Typical Performance]

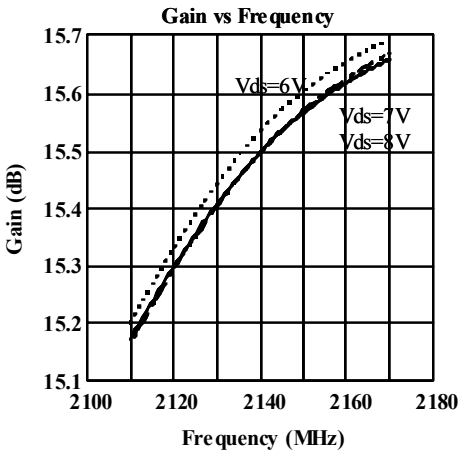
KP027J Application Circuit
Vds=8V, Ids=100mA, Tc=25°C
Frequency characteristics were measured with Pout at 13dBm.

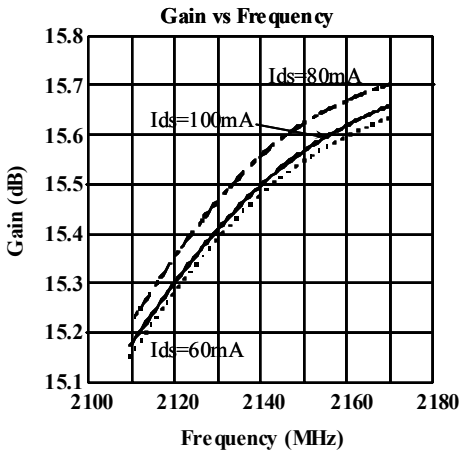












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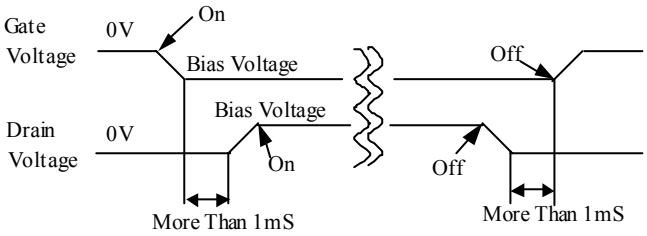
♦Caution: Power Supply Sequence

For safe operation, electric power should be supplied in following sequence. First, the negative voltage should be applied on the gate, and the voltage should be more negative than the pinch-off voltage when you turn on the power supply. Then, drain bias can be applied. Finally, you can turn on the RF signal.
When turning off the power supply, the sequence should be (1)RF signal (2)Drain (3)Gate.

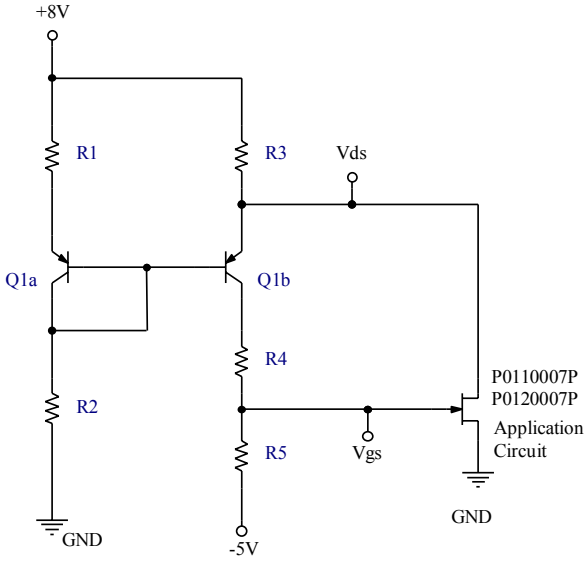


♦Bias Circuit

[Passive Biasing]
If you use a fixed bias circuit, you sometimes need to control the gate bias to get the same Ids, since the devices have some margin of pinch-off voltage (Vp) variation depending on the wafer lots. If you employ a fixed Vgs biasing for your system, you should closely monitor the drain current, particularly when new wafer lots are introduced.

[Active Biasing]
We recommend using an active bias circuit, which can eliminate the influence of Vp variation. An example of an active bias circuit called "current mirror " is shown below. Here, two PNP transistors having the minimum variation of Ibe characteristics are used. These transistors adjust Vgs by changing Vds automatically. It will realize the constant current characteristics, regardless of the temperature.
The circuit should be connected directly in line with where the voltage supplies would be normally connected with the application circuit. Of course a matching circuit is required, but it is not shown in this figure.

[Note]
In the measurements of RF performance (Pout vs Pin, etc) using the application circuit described before, the active bias circuit herein was not utilized. The application circuits were biased directly from two power supplies.



Vds	+7.9V
Ids	100mA
Q1	UMT1N (Rohm)
R1	33Ω 1/10W
R2	2.4kΩ 1/10W
R3	1Ω RL series (SUSUMU)
R4	1kΩ 1/10W
R5	1.3kΩ 1/10W

If you used Ids other than 100mA, you can calculate the resistance values as follows:

R4 set to be 1kΩ
I_1: Ic of Q1a I_2:Ic of Q1b
V_{be1}: Vbe of Q1a V_{be2}: Vbe of Q1b

$R1=(+8V-Vds+V_{be2}-V_{be1})/I_1=(+8V-Vds)/I_1$
$R2=(Vds-V_{be2})/I_1$
$R3=(+8V-Vds)/(Ids+I_2)$
$R5=|-5V-Vgs|/I_2$

♦Attention to Heat Radiation

In the layout design of the printed circuit board (PCB) on which the power FETs are attached, the heat radiation to minimize the device junction temperature should be taken into account, since it significantly affects the MTTF and RF performance. In any environment, the junction temperature should be lower than the absolute maximum rating during the device operation and it is recommended that the thermal design has enough margin.

The junction temperature can be calculated by the following formula.

$T_{jmax}=(Vds*Ids-P_{out})(R_{th}+R_{board}+R_{hs})+T_a$

P_{out}: Output power
R_{th}: Thermal resistance between channel and case
R_{board}: Thermal resistance of PCB
R_{hs}: Thermal resistance of heat sink
T_a: Ambient temperature
T_{jmax}: Maximum junction temperature

Generally, there are two ways of heat radiation. One is the plated thru hole and the other is the heat sink. Key points will be illustrated in each case below. Note that no measure against oscillation is adopted in the figures. In the design of circuit and layout, you should take stabilizing into account if necessary.

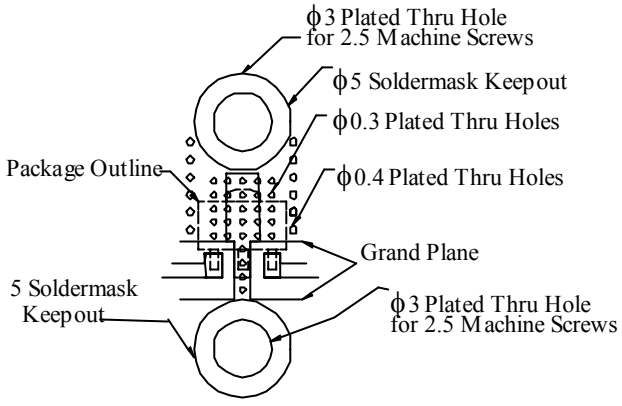
[Using Thru Hole]

□Multiple plated thru holes are required directly below the device.

□Place more than 2 machine screws as close to the ground pin (pin 4) as possible. The PCB is screwed on the mounting plate or the heat sink to lower the thermal resistance of the PCB.

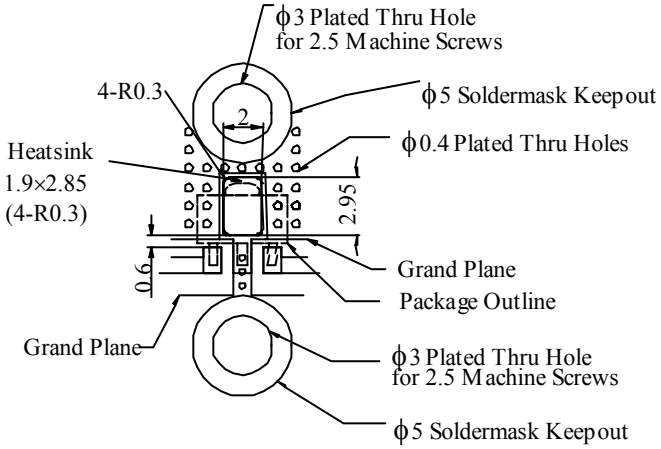
□Lay out a large ground pad area with multiple plated thru holes around pin 4 of the device.

□The required matching and feedback circuit described in the application circuit examples should be connected to the device, although it is not shown in the figure below.



[Using Heat Sink]

If you cannot get the junction temperature lower than the absolute maximum rating only with the plated thru holes, then you need to employ the heat sink. Attaching the heat sink directly under pin 4 of the device improves the thermal resistance between junction and ambient.



[Note]

□Ground/thermal vias are critical for the proper device performance. Drills of the recommended diameters should be used in the fabrication of vias.

□Add as much copper a s possible to inner and outer layers near the part to ensure optimal thermal performance.

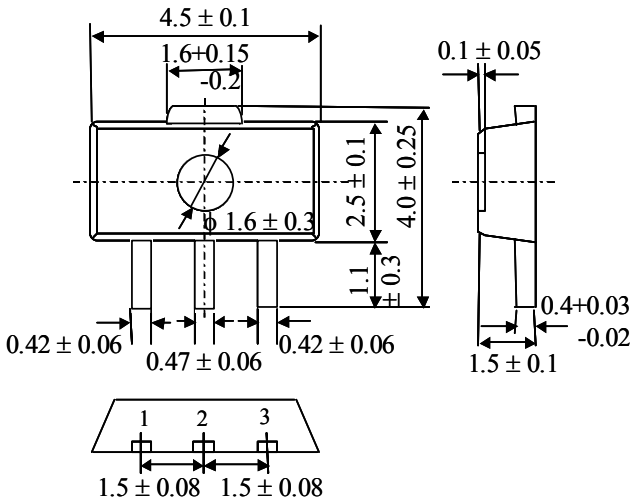
□Mounting screws can be added near the part to fasten the board to heat sink. Ensure that the ground/thermal via region contacts the heat sink.

□Do not put solder mask on the backside of the PCB in the region where the board contacts the heat sink.

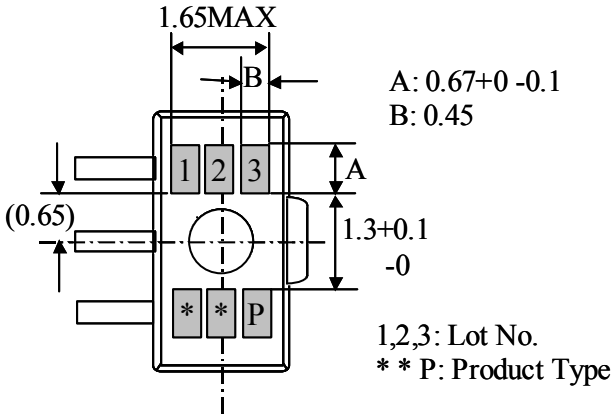
□RF trace width depends upon the PCB material and construction.

□Use 1 oz. Copper minimum.

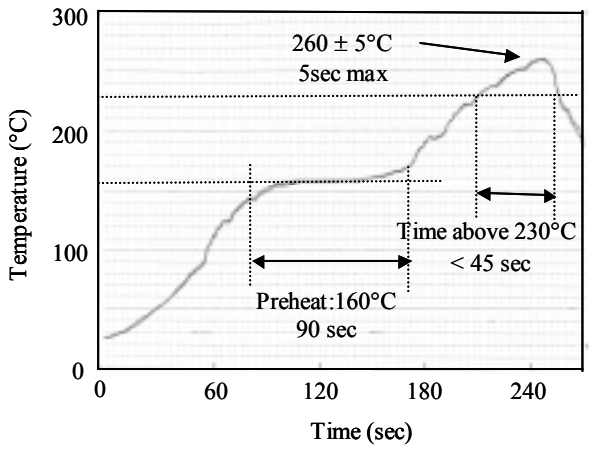
♦Package Drawing



♦Laser Marking



♦Convection Reflow Profile (Recommended)



[Note]

The reflow profile is different from the one for Sn-Pb plating.

If you use a soldering iron to attach the devices, please beware of the followings.

(1) The tip of the iron should be grounded. Or you should use an iron that is electrostatic discharge proof.

(2) The temperature of the iron tip should be lower than 240 °C and the soldering should be completed within 10 seconds.

♦Attention to ESD

Generally, GaAs devices are very sensitive to electrostatic discharge (ESD). To reduce the ESD damage, please pay attention to the followings. The devices should be stored with the electrodes short-circuited by conductive materials. The workstation and tools should be grounded for safe dissipation of the static charges in the environment. The workpeople are to wear anti-static clothing and wrist straps. For safety reasons, resistance of 10MΩ or so should exist between workpeople and ground.

♦Attention to Moisture

The moisture sensitivity level (MSL) of P0120007P is 3, which means that the "floor life" is 168 hours below 30°C with relative humidity (Rh) of 60%.

The devices are usually shipped in moisture-resistant alumina-laminated packages. After breaking the packages, they are to be stored under normal temperature and humidity (5-35°C, 45-75%), with no corrosive gases or dust in the environment. Assemble the devices within 168 hours after breaking the package, or you have to bake them at 85°C for 24 hours before assembling.

♦Reliability and Environmental Issues

The detailed reliability information can be seen in ***Reliability and Quality Assurance***, which you can download from our web site.

SEI's Yokohama Works, where the devices are manufactured, has been accredited ISO-14001 since 1999. We control the toxic materials in our products in accordance with PRTR regulation.

♦ Lead and Fluoride

To realize Pb-free products, Sn-Bi is used for the lead frame plating. Any fluoride that has been determined by the Montreal agreement is not used in the products.

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♦Caution

GaAs FET chips are used in P0120007P. For safety reasons, you should attend to the following matters:
(1) Do not put the products in your mouse.
(2) Do not make the products into gases or powders, by burning, breaking or chemical treatments.
(3) In case you abandon the products, you should obey the related laws and regulations.

♦Technical Inquiries are Welcome

SEI welcomes technical questions from any customers. The e-mail is GaAsIC-ml@ml.sei.co.jp. You can also contact our regional offices as below.

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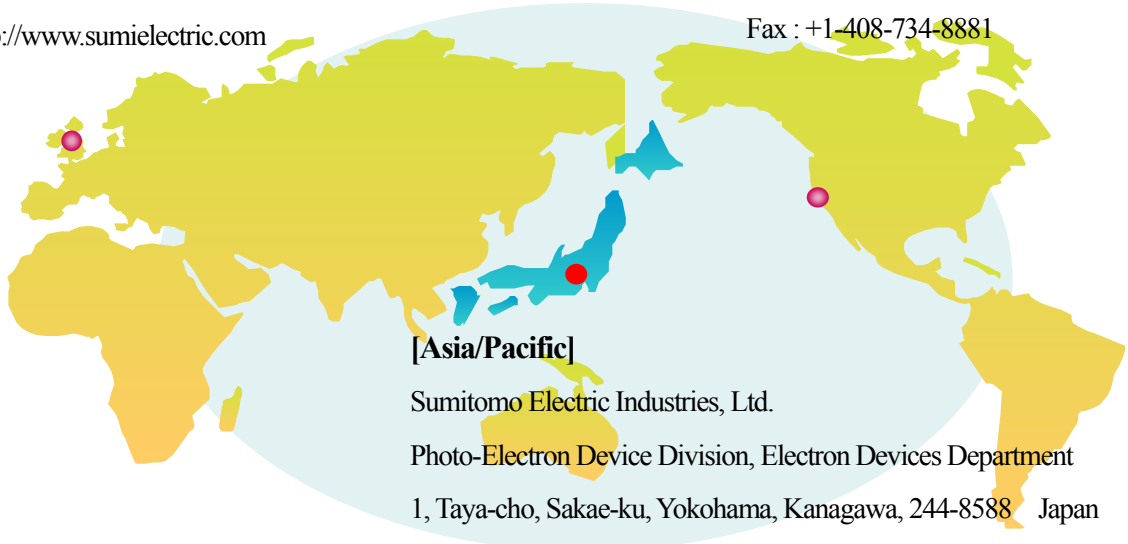

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